Supermetallic conductivity in bromine-intercalated graphite


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(Received 13 November 2009; published 16 March 2010)

Exposure of highly oriented pyrolytic graphite to bromine vapor gives rise to in-plane charge conductivities which increase monotonically with intercalation time toward values (for ~6 at % Br) that are significantly higher than Cu at temperatures down to 5 K. Magnetotransport, optical reflectivity and magnetic susceptibility measurements confirm that the Br dopes the graphene sheets with holes while simultaneously increasing the interplanar separation. The high-room-temperature mobility (~5 x 10^4 cm^2/V s) and resistance anisotropy together with the reduced diamagnetic susceptibility of the intercalated samples suggests that the observed supermetallic conductivity derives from a parallel combination of weakly coupled hole-doped graphene sheets.

DOI: 10.1103/PhysRevB.81.115428

PACS number(s): 81.05.U-, 71.20.-b, 72.15.-v

I. INTRODUCTION

At the simplest level graphite can be thought of as an ordered stacking of weakly coupled graphene sheets. Delamination or deconstruction of graphite into isolated graphene sheets for experimental characterization by mechanical means has nucleated intense experimental and theoretical investigation into the electronic properties of this two-dimensional (2D) carbon allotrope. The presence of Dirac-like electronic excitations, an anomalous integer quantum Hall effect, and signature sensitivity to different types of disorder are but a few of the fascinating phenomena emerging from these studies. Bernal stacked graphite with an interplanar spacing c = 3.4 Å manifests properties that are precursors to the unusual behaviors associated with graphene and few-layer graphene. For example the presence of Dirac fermions near the H point in the Brillouin zone has been detected by angle-resolved photoemission spectroscopy.

Graphite intercalation compounds (GICs) have long been recognized as having unusual and sometimes surprising properties. In this study we take the approach of using bromine (Br) intercalants to simultaneously dope and separate the planes of graphite and thereby begin an approach to the limit where the interplanar coupling is sufficiently weak to assure that the resulting in-plane conductivity can be considered as the parallel contribution of relatively independent doped graphene sheets. Since the band structure of graphite gives nearly equal numbers of electrons and holes, with a density on the order of ~10^4 carriers per carbon atom, a small charge transfer between the intercalate and the adjacent carbon planes can result in a significant increase in free carriers per carbon. We find that random site interplanar doping with bromine to concentrations (~6 at %) gives rise to a pronounced decrease of the in-plane resistivity \( \rho_{ab} \) to “supermetallic” values that are significantly lower than Cu over the temperature range 300 K > T > 1.7 K. Hall and x-ray photoelectron spectroscopy (XPS) measurements confirm that the Br dopant acts like an acceptor, thus hole doping the graphene planes. Optical reflectance measurements confirm the supermetallic in-plane conductivity and further reveal a doping-induced increase of mobility and carrier density. The diamagnetic susceptibility decreases toward zero as would be expected for isolated graphene sheets, and there is no evidence of diamagnetic screening that might be associated with superconducting fluctuations. At T = 5 K the inferred sheet resistance per graphene plane of less than 1 \( \Omega \) is significantly lower than reported for isolated graphene sheets either biased by an adjoining gate or doped with impurity atoms.

II. EXPERIMENTAL

A. Sample preparation and characterization

The highly oriented pyrolytic graphite (HOPG) samples are cut from a single piece having 0.5° mosaic spread and typically have dimensions on the order of 1–5 mm. The samples are exposed to Br gas at room temperature in closed tubes for various intercalation times and then removed and measured in a four-contact arrangement using a LR700 17 Hz resistance bridge at temperatures and fields along the c axis in the ranges 5 K < T < 300 K and -7 T < B < 7 T, respectively. In highly anisotropic samples, precautions are needed to assure uniform current density between voltage leads. We therefore used platelet (brick) shaped samples for the \( \rho_{ab} \) (\( \rho_c \)) measurements while taking care to assure uniformly contacted current leads for each case. Results for the resistivity of a given sample are reproducible to 1% and for twelve different samples cut from the same piece reproducible to 3%. After each measurement, additional intercalations could be made on the same sample. Weight uptake and volume increase, measured to an accuracy of ~3%, give a good measure of the correlation between Br concentration and doping time \( t_{Br} \).

To characterize further the differences between pristine HOPG and the Br-doped samples, we also used x-ray diffraction (XRD), optical reflectance, Auger electron spectroscopy (AES), scanning electron microscopy (SEM), and x-ray photoelectron spectroscopy (XPS). SEM characterization did not detect any intercalation induced changes in surface morphology. The \( 2\theta \) XRD scans revealed only (00l) reflections that were shifted to lower angle (increased lattice spacing) with increased intercalation time and hence the concentration of Br between the graphene layers. This expansion is in
agreement with the observed swelling of the sample. There were no additional reflections indicating staging or, equivalently, ordering of the Br intercalants. Optical reflectance measurements were made at 300 K using a Bruker 113v Fourier spectrometer over the range 40–5000 cm\(^{-1}\) (5–600 meV) and a Zeiss MPM 800 microspectrophotometer over 4000–40 000 cm\(^{-1}\) (0.5–5 eV). The low-frequency limit is set by the signal-to-noise and diffraction limitations of our small samples. Br LMM Auger peaks are observed to be located at 1396, 1442, and 1476 eV for Br exposure times \(\geq 30\) minutes. The samples were repeatedly cleaved and re-measured to probe the Br concentration at different depths of the sample; the peak heights for a given sample remained constant to within 5%. The Br concentrations extracted from the Auger measurements agreed well with the weight-uptake/volume-expansion measurements.

XPS spectra of bromine doped HOPG samples were measured with a 99% monochromatized Mg x-ray source with energies up to 1100 eV. Satellite peaks shifted by \(\sim 10\) eV were barely visible. Elemental percentage analyses were found to be consistent with AES and weight uptake measurements. The C:1s electron binding energy measured relative to the Fermi level is observed to be at 284.5 eV for pristine and at 284.0 eV for the \(t_{\text{Br}}=70\) min sample. At first sight, the reduction in the C:1s binding energy by 0.5 eV contradicts the acceptor nature of Br, i.e., the more positively charged carbon should, for fixed \(E_F\), have a higher binding energy. However, similar trends/findings in donor (acceptor) type intercalants and associated increase (decrease) in C:1s binding energy have been reported in the literature for different compounds\(^{11,12}\) and attributed to the change in \(E_F\) before and after intercalation. In brominated HOPG, \(E_F\) is negative and significantly larger in magnitude compared to pristine HOPG and the C:1s binding energy is thus measured with respect to the lower \(E_F\) of the hole-doped system. Accordingly, the increase in the C:1s binding energy is more than compensated for by the decrease in \(E_F\), giving an overall decrease in the C:1s peak position as observed. The XPS method thus gives another way of estimating the change in Fermi level and implies a \(\sim -0.5\) eV change in \(E_F\) after hole doping to 6 at % Br.

B. Electrical transport measurements

Figure 1(a) shows the dependence of \(\rho_{\text{ab}}\) on Br intercalation time at \(T=300\) K. Although the initial linear dependence is not understood, we note that after 70 min, \(\rho_{\text{ab}}\) appears to saturate at a value that is approximately a factor of five lower than the room-temperature value (1.7 \(\mu\Omega\)cm) of copper indicated by the horizontal dashed line. Our interpretation of how the carrier density \(N\), the scattering time \(\tau\) and the effective mass \(m^*\) are affected by Br intercalation is based on using the Drude model in which the conductivity \(\sigma\) of each contributing band is \(\sigma=ne^2\tau/m^*\equiv ne\mu\), where the mobility \(\mu=e\tau/m^*\).

In Fig. 2 we show the evolution of the field \(B\) dependent transverse resistance \(\rho_{xy}\) for intercalation times \(t_{\text{Br}}\) ranging from \(t_{\text{Br}}=0\) (pristine HOPG) to \(t_{\text{Br}}=70\) min. The data for pristine HOPG are well fit by the expression for the two-band model,\(^{6}\)

\[\rho_{xy}(B) = \frac{-n_h \mu_h^2 + n_h \mu_e^2}{1 + \mu_e^2(n_h - n_e)^2 + \mu_h^2(n_e - n_h)^2} \approx \frac{-n_h \mu_h^2}{1 + \mu_e^2(n_h - n_e)^2 + \mu_h^2(n_e - n_h)^2}, \]

where \(\rho_{xy}(0)\) is the B=0 in-plane resistivity and the subscripts \(e\) and \(h\) refer respectively to the electron and hole bands. The obtained fitting parameters are \(n_e=2.0(1) \times 10^{19}\) cm\(^{-3}\), \(n_h=1.6(1) \times 10^{19}\) cm\(^{-3}\), \(\mu_h = 4700(100)\) cm\(^2\)/V·s, and \(\mu_e=6800(100)\) cm\(^2\)/V·s showing that our pristine HOPG is slightly hole doped with similar mobilities in each band. In graphite, Eq. (1) is applicable for \(\mu B \geq 1\), when \(\rho_{xy}(B)\) is quadratic in \(B\).\(^{13}\) At \(T=300\) K,
\(\mu B=1\) corresponds to \(B=0.3\ T\) in pristine graphite, so Eq. (1) describes most of the field range presented in Fig. 2. With increasing \(t_{\text{Br}}\), the quadratic dependence of \(\rho_{\text{ab}}(B)\) occurs over a decreasing field range, thus restricting the range of validity of Eq. (1). Constrained by this requirement, we extract a square-root dependence of \(N\) on \(t_{\text{Br}}\) shown in Fig. 1(b). As seen in Fig. 2, the low-field slope, which is positive for \(t_{\text{Br}}\approx 20\ \text{min.}\), decreases with increasing Br concentration and becomes linear for the highest \(t_{\text{Br}}\), thus indicating that Br is hole doping the graphene sheets with a carrier density \(N=n_h\) dominated by holes.

The temperature-dependent resistivity data of panels (a) and (b) of Fig. 3 show that the resistivity scales for \(\rho_{\text{ab}}(\rho_{\text{c}})\) decrease (increase) as \(T\) is reduced from 300 K to 5 K. The positive curvature for samples with \(t_{\text{Br}}=70\ \text{min.}\) is consistent with the notion that the doping is sufficient to guarantee \(E_F \approx k_B T\) in contrast to pristine HOPG and the lightly doped samples where \(E_F \approx 300\ K\) and significant variation of \(N\) with \(T\) leads to a negative curvature of \(\rho_{\text{ab}}(T)\). The ratio \(\rho_{\text{ab}}(300\ K)/\rho_{\text{ab}}(5\ K)\approx 47\) for the sample with \(t_{\text{Br}}=70\ \text{min.}\) is higher by more than a factor of 10 than the same ratio (4.0) for pristine HOPG. In contrast to \(\rho_{\text{ab}}\), \(\rho_{\text{c}}\) increases with increasing \(t_{\text{Br}}\) due to the presence of Br intercalants acting like a negative pressure pushing the planes apart [see schematic inset of Fig. 1(a)], thereby resulting in decreased interplanar tunneling. With the application of positive pressure the interplanar spacing decreases and there is a corresponding decrease in \(\rho_{\text{c}}\).\(^{12}\) The hole doping of the planes (decreasing \(\rho_{\text{ab}}\)) concomitant with an increasing interplanar spacing (increasing \(\rho_{\text{c}}\)) leads to an anisotropy ratio \(\rho_{\text{c}}/\rho_{\text{ab}}\) at 5 K approaching \(10^7\), a factor of 1000 greater than measured for pristine HOPG at the same temperature.

C. Optical measurements

With increasing \(t_{\text{Br}}\), the far infrared and midinfrared reflectance increase dramatically as shown in Fig. 4(a). This increase in reflectance implies an associated increase in optical conductivity which is borne out by a Kramers–Kronig analysis.\(^{15}\) We used a Drude extrapolation at low frequencies and a power-law behavior at high frequencies, with the results shown in Fig. 4(b). Note that the optical conductivity curves include frequencies (dashed lines) where we used the extrapolation; the good agreement with the dc conductivity in Fig. 1(a) and the good fits to the reflectance provide confidence that the behavior is as shown. As the doping proceeds, the low-frequency conductivity increases and the spectral weight (the area under the curve) increases significantly [Fig. 4(b)]. The full width of this Drude-like peak represents the carrier scattering rate \(\tau^{-1}\) which at the highest doping is decreased by a factor of five relative to the pristine sample.

We also note in the raw reflectance data of Fig. 4(a) the appearance of a phonon mode around 1580 cm\(^{-1}\). This mode, which appears to strengthen and develop a Fano lineshape with Br intercalation, can barely be seen as a small feature above the line in the conductivity spectra of Fig. 4(b). To show this feature in more detail, we have magnified the appropriate region by a factor of 1000 as shown in Fig. 5. The weak optical phonon near 1588 cm\(^{-1}\) increases in strength by nearly a factor of four and red shifts by 3 cm\(^{-1}\).
These trends are consistent with prior results, which show that intercalation changes the lineshape, lowers the frequency, and also leads to higher oscillator strength of this mode. Metallic behavior thus persists out to these energies in the strongly intercalated samples.

From the sum rule on the optical conductivity, we can relate the low-energy spectral weight to the carrier density. The spectral weight also affects the real part of the dielectric function, \( \varepsilon_1(\omega) \), which for free carriers follows \( \varepsilon_1(\omega)=1-\omega_p^2/\omega^2 \), where \( \omega_p^2=4\pi Ne^2/m^* \) is the plasma frequency. The inset of Fig. 4(b) shows \( \varepsilon_1(\omega) \) plotted vs \( 1/\omega^2 \); the slopes of these plots give the carrier density, which is seen to increase by more than a factor of eight with increasing \( t_{Br} \). That the curves are straight lines implies strongly that a free-carrier (metallic) picture of the low-energy electrodynamics is an accurate view of the intercalated graphite. The dc resistivities inferred from the Drude fit to the infrared reflectance measurements are shown as blue triangles in Fig. 1(a). Because the reflectance measurements are made without placing electrical contacts on the sample, the inferred dc conductivities of Fig. 4(b) give independent confirmation of the supermetallic conductivity inferred from transport measurements.

D. Magnetization measurements

Figure 6 shows that the temperature-dependent dc diamagnetic susceptibility \( \chi \) (field parallel to \( c \) axis) decreases with increasing \( t_{Br} \). Our room-temperature value for pristine graphite, \( \chi=-21.3 \times 10^{-6} \) emu/g, is in good agreement with previous experiments. The susceptibility decreases by a factor of three for \( t_{Br}=90 \) min. This decrease in \( \chi \) with increased hole doping of the graphene planes is qualitatively understood by realizing that as the Fermi energy moves away from the neutrality point (\( n_s=n_c \)) of pristine graphite, the cyclotron mass \( m^* \) increases and \( \chi \propto 1/m^* \) decreases, approaching the limit of exponentially weak diamagnetism for single-plane Dirac fermions. Importantly, there is no signature of superconductivity, which, if associated with the giant conductivity, would become manifest as an increase in diamagnetism at some characteristic temperature.

III. DISCUSSION

Graphite intercalation compounds in the dilute limit are well known to exhibit enhancements of room-temperature conductivity which, with increasing intercalant concentration, saturate to modest values \( \sim 10 \) times the pristine value. The surprising and unexpected result presented here is that for uniformly dispersed nonstaged Br dopants at relatively low concentrations near 5–6 at\% the conductivity can justifiably be referred to as “supermetallic.” To make comparisons to single-layer graphene, we convert our \( \rho_{ab} \) measurements to resistance per square \( R_g \) of each carbon plane and see that \( R_g \) near 1000 \( \Omega \) for HOPG at 300 K decreases to less than 0.5 \( \Omega \) at \( 5 \) K for intercalated samples with \( t_{Br}=70 \) min. To our knowledge, there are no reports of such a low \( R_g \) for graphene.

The experimental results raise many questions, e.g., since doping introduces disorder, why does the conductivity increase? At high-doping level, most of the carriers (holes) come from negatively charged acceptors, so we have a system, in which the number of carriers is approximately equal to the number of scattering centers. On the other hand, since the Fermi energy shifts downward and increases with doping, the scattering cross-section decreases, so we have two competing effects. Assuming for a moment that the scattering cross-section is of the 2D classical Rutherford form \( A_R \sim e^2/E_F \), that \( E_F \) obeys the 2D scaling \( E_F \propto n_{ac} \), where \( n_{ac} = n_{ac}^0 \) is the number density of acceptors per layer, and estimating the mean free path as \( l=1/n_{ac}A_R \), we arrive at a simple result for the parameter \( k_F l \), which characterizes purity of a material: \( k_F l \sim 1/r_s \), where \( r_s \) is the average intercarrier distance measured in Bohr radii. Already in pristine graphite, \( r_s \approx 1 \) (Ref. 18) and it decreases further with doping, so this simple model predicts that the material becomes “cleaner” with doping, concomitant with an increase in the 2D conductivity, which is proportional to \( k_F l \).

In reality, this simple picture is modified significantly due to effects of screening. To see this in more detail, we consider the screening mechanism in doped graphite. In pristine graphite, the Fermi energy \( E_F \approx 225 \) meV is on the order of...
the hopping energy between the next-to-nearest graphene layers, $\gamma_c$. Upon doping, the Fermi energy increases. We consider two limiting cases: (i) $\gamma_c \ll E_F \ll \gamma_1$ and (ii) $\gamma_1 \ll E_F \ll \gamma_0$, where $\gamma_1 \approx 0.3$ eV is the nearest-layer hopping and $\gamma_0 \approx 3.2$ eV is the nearest-neighbor hopping in the graphene plane. In the first case, graphite is the “bilayer regime”$^{18}$; the energy spectrum of holes is approximately $E_k = -\hbar^2 k_z^2 / 2m_1(k_z)$, where $m_1(k_z) = m_0 \cos(k,z,c)/2$ is the $k_z$ dependent in-plane mass with $m_0 = \gamma_1 / v_0^2$, $v_0 = 10^8$ cm/s is the Dirac velocity, and $c = 6.8$ Å is the $c$ axis lattice constant. The density of states (per spin and per K point of the graphite Brillouin zone) in this regime $\nu = \gamma_1 / \hbar^2 \pi^2 v_0^2 k_z^2$ does not depend on the electron energy. In the second case, graphite is in the graphene regime: the spectrum is Dirac-like $E_k = -\hbar v_k |q|$ and the density of states $\nu = e/2 \pi^2 \hbar v_0^2 k_z$ increases linearly with energy $e$. In the Thomas–Fermi model, the square of the screening wave vector is $\kappa^2 \approx 16 \pi e^2 \nu$. Although $\kappa$ increases with $E_F$, it still remains much smaller than the reciprocal lattice constant for not too high dopings. Indeed, it is easy to see that $\kappa^2 c^2 \sim (c/\kappa_{03}) (E_F / \gamma_1)$ in the graphene regime, where $\kappa_0^2 = \epsilon_0^2 \hbar^2 / 2\pi^2 m_0 \approx 50$ Å for the background dielectric constant $\epsilon_0 = 5$. Therefore, $\kappa^2 c^2 \ll 1$ for $E_F \ll 10 \gamma_1 = \gamma_0$. Accordingly, in both the bilayer and graphene regimes screening is not sensitive to details of the spectrum, all of which are incorporated into the density of states. In the continuum limit, with the screening radius large compared to the lattice constant, the screened potential is isotropic.

The above arguments allow us to model the potential of a single charged acceptor by a simple Thomas–Fermi form,

$$V(q) = -\frac{4\pi e^2}{q_0^2 + q_z^2 + \kappa^2},$$

where $h q_0$ and $h q_z$ are the in-plane and $c$-axis momentum transfers of charge carriers. The scattering time can be then obtained from the Fermi Golden Rule

$$\frac{1}{\tau} = \frac{2\pi}{\hbar} \int \frac{d^2 q_0}{(2\pi)^2} \int \frac{d^2 q_z}{2\pi} V(q) \delta (\epsilon_{k+q_k,\epsilon} - \epsilon_{k+q_k,\epsilon}).$$

Another simplification comes from the fact that $q_0$ is bounded by twice the in-plane radius of the Fermi surface $k_{\text{F}0} \sim (n_0 \epsilon)$, which is smaller than $\kappa$ for not too high dopings. This implies that one can neglect $q_0$ in Eq. (2). On the other hand, as typical $q_z \sim \kappa \ll a / e$, one can neglect $q_z$ in the energies entering the $\delta$ function in Eq. (3). The integral over $q_z$ can be then performed independently of that over $q_0$ and yields an effective coupling constant for in-plane scattering $V = \int d^2 q_0 V^2(q) / 2\pi^2 = 4\pi^2 e^4 / \kappa^2$. In terms of $V$, the scattering rate can be written as

$$\frac{1}{\tau} = \frac{2\pi}{\hbar} n_0 \bar{\nu}_{\text{2D}},$$

where

$$\bar{\nu}_{\text{2D}} = \int \frac{d^2 q_0}{(2\pi)^2} \delta (\epsilon_{k+q_k,\epsilon} - \epsilon_{k+q_k,\epsilon}),$$

is the effective density of states per graphene layer. Accordingly, charged acceptors act effectively as short-range scatter-
our intercalated graphite as an ordered stack of isolated graphene sheets each of which is dominated by Dirac fermions, we believe our results illustrate the emergence of intriguing phenomenology at the graphite/graphene boundary accessed by intercalation.

ACKNOWLEDGMENTS

We thank D. Arenas, H.-P. Cheng, V. Craciun, J. E. Fischer, E. Lambers, and B. Shklovskii for useful discussions. This research was supported by the NSF and DOE under Grants No. DMR-0704240(AFH) and No. DE-FG02-02ER45984(DBT).

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